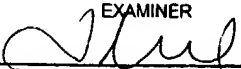


<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  <b>(PTO-1449)</b>				ATTY. DOCKET NO. <b>60188-575</b>		SERIAL NO. <b>Continuation of Appl. No. 10/107,334</b>	
				APPLICANT <b>Takashi NISHIKAWA, et al.</b>			
				FILING DATE <b>November 07, 2003</b>		GROUP <b>1775</b>	
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code(s) (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
<i>SM</i>		US 6,469,334	10/2002	Arita et al.			
<i>SM</i>		US 6,265,353	07/2001	Kinder et al.			
<i>SM</i>		US 5,514,484	05/1996	Nashimoto			
<i>SM</i>		US 6,214,712	04/2001	Norton			
<i>SM</i>		US 4,479,297	10/30/1984	Mizutani et al.			
		US					
<b>FOREIGN PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Code(s)-Number(s)-Kind Code(s) (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
<i>SM</i>		JP 57-211267	12/25/1982	Toshiba Corp.			
<i>SM</i>		JP 8-162614	06/21/1994	TDK Corp.			
<i>SM</i>		JP 10-231196	09/02/1998	Sony Corp.			
<i>SM</i>		JP 10-199999	07/31/1998	Asahi Chem Ind. Co Ltd.			
<i>SM</i>		JP 9-172097	06/30/1997	Asahi Chem Inc. Co. Ltd.			
		JP 2000-344599	12/12/2000	Sony Corp.			
<b>OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
<i>SM</i>		I. SAKAI et al., "Preparation and Characterization of PZT Thin Films on CeO <sub>2</sub> (111)/Si(111) Structures", Jpn. J. Appl. Phys., Vol. 35, Part 1, No. 9B, pages 4987-4990, September 1996.					
<i>SM</i>		T. INOUE et al., "Intermediate Amorphous Layer Formation Mechanism at the Interface of Epitaxial CeO <sub>2</sub> Layers and Si Substrates", Jpn. J. Appl. Phys., Vol. 32, Part 1, No. 4, pages 1765-1767, April 1993.					
<i>SM</i>		S. YAGASHI et al., "Epitaxial Growth of CeO <sub>2</sub> Films on Si(111) by Sputtering", Jpn. J. Appl. Phys., Vol. 33, Part 1, No. 1A, pages 270-274, January 1994.					
<i>SM</i>		H. KOINUMA et al., "Ceramic layer epitaxy by pulsed layer deposition in an ultrahigh vacuum system", Appl. Phys. Lett., 58(18), pages 2027-2029, 6 May 1991.					
<i>SM</i>		T. INOUE et al., "Texture Structure Analysis and Crystalline Quality Improvement of CeO <sub>2</sub> (110) Layers Grown on Si(100) Substrates", Jpn. J. Appl. Phys., Vol. 31, Part 2, No. 12B, pages L1736-L1739, 15 December 1992.					
<i>SM</i>		M. YOSHIMOTO et al., "In Situ RHEED Observation of CeO <sub>2</sub> Film Growth on Si by Laser Ablation Deposition in Ultrahigh-Vacuum", Japanese Journal of Applied Physics, Vol. 29, No. 7, pages L1199-L1202, July 1990.					
EXAMINER 				DATE CONSIDERED <b>3/4/04</b>			

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

\* - not received